Application of Au@SiO$_2$ Plasmonic Nanoparticles at Interface of TiO$_2$ Mesoporous Layers in Perovskite Solar Cells

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ABSTRACT—To investigate the plasmonic effect in perovskite solar cells, the effect of depositing Au@SiO$_2$ nanoparticles on the top and the bottom of mesoporous TiO$_2$ layers was studied. First, Au@SiO$_2$ nanoparticles were synthesized. The particles were then deposited at the different interfaces of mesoporous TiO$_2$ layers. Although the two structures show approximately similar optical absorption, only cells with Au@SiO$_2$ nanoparticles deposited at the bottom of the mesoporous TiO$_2$ layers demonstrated an improved photocurrent performance compared to the reference cells. This structure shows a short-circuit current density (JSC) of 20.7 mA/cm$^2$ and open circuit voltage of 1081 mV. This enhancement may be attributed either to the interface surface engineering or plasmonic resonance of Au@SiO$_2$ nanoparticles depends to the NPs size and position.

KEYWORDS: Photovoltaic, Perovskite solar cells, Au@SiO$_2$ nanoparticles, Plasmonic nanoparticles, Core-shell.

I. INTRODUCTION

In recent years, organic–inorganic perovskites materials have been widely investigated as light harvester in solar cells. They have superior properties including direct band gap, large absorption coefficients, and high carrier mobility which enabling us to be used as a light harvester in a solar cell [1]. The Maximum power conversion efficiency (PCE) of perovskite based solar cells is reported from 3.8% in 2009 [2] to over 22.1% in recent years [3]. To increase efficiency, it is necessary to extend light absorption spectrum, by means of applying noble metal nanoparticles (NPs), increase the active layer thickness, inserting scattering layers, and back reflectors layers or other light trapping elements [4]–[6]. The addition of noble metal gold (Au), silver (Ag) and aluminum (Al) NPs in the hole transport layer (HTL) of planar inverted perovskite solar cells showed that electron extraction and in turn device efficiency are enhanced [7]. An effective method has also been investigated in perovskite devices to achieve efficient performance by combinational use of Au NPs insulating by MgO [8]. Also, different amount of Au@SiO$_2$ core–shell NPs have been deposited as a modifier of the mp-TiO$_2$ layer in perovskite solar cells, and the enhanced in device performance and increase in light absorption are reported [9].

Au and Ag are the most commonly used plasmonic materials, and they have also been combined with oxide cores or shells [10]–[12]. The maximum PCE of 16.3% was reported in perovskite solar cell having plasmonic structure [11]. More recently, the role of NPs in perovskite solar cells has been investigated theoretically [13],[14]. They showed Au@SiO$_2$ core-shell NPs provide optical absorption enhancement in perovskite solar cells, where the perovskite material itself has relatively poor absorption. Also, they showed
Au@SiO₂ NPs with a SiO₂ shell thickness of ~1 nm provided greater absorption enhancement than the NPs with thicker shells [13]. In previous work, our group studied the plasmonic effects of Ag NPs (Ag NPs without shell) on the photovoltaic characteristics of mesoporous heterojunction HTL-free perovskite solar cells [15]. Most recently we have studied and reported the dramatic role of Au@SiO₂ NPs in the perovskite solar cells interfaces, where, the use of reduced quantities of highly stable inorganic compounds modified the PSC interface instead of the extensively used organic compounds [16].

In this study, we studied two methods of photocurrent enhancement on perovskite solar cells in which Au@SiO₂ NPs were deposited on the bottom and the top of a mesoporous TiO₂ (mp-TiO₂) as an interface layer (Fig.1). It is shown that the both structures by using Au@SiO₂ NPs increases the short-circuit current density of the fabricated cell, while enhancement by using Au@SiO₂ NPs was deposited on the bottom of mp-TiO₂ is more significant.

II. EXPERIMENTAL Procedure

A. Cell Fabrication

NP Synthesis. An Au sol is prepared based on Turkevich procedures [17]. Briefly, 250 mL of HAuCl₄ solution (1 mM), 25 mL of 1% sodium citrate solution was added, with boiling and vigorous stirring. After 10 min, the mixture produces a stable, deep-red dispersion of Au particles. An average diameter of Au was around 11 nm.

For Au@SiO₂ core/shell NPs Synthesis, Au@SiO₂ core-shell NPs were prepared according to the synthetic protocol of Liz-Marzan [18]. Briefly, 2.5 mL freshly prepared 1 mM aqueous solution of (3-aminopropyl) trimethoxysilane (APS) was added to 500 mL of the Au solution under vigorous magnetic stirring. The mixture was stirred for 15 min to ensure complete the amine groups with the Au surface. Then the 20 mL active silica with lowering the pH of a 0.54 wt % sodium silicate solution was added to 500 mL of the surface-modified Au solution under vigorous magnetic stirring. After stirring for 24 h, the NPs were collected by centrifugation at 15000 rpm for 1 h, washed three times with deionized water, and finally re-dispersed in ethanol. The thickness of silica shell was about 1.4 nm with an absorption peak at ~550 nm in water, as shown in Fig. 2.
optical absorption spectrum of the core-shell sample in water.

Perovskite solar cells were fabricated on a structure based on Fluorine-doped Tin Oxide glass (FTO) glasses, which were partially etched using 2 M HCl and Zn powder, cleaned by the following procedure: cleaning with soap (Hellmanex) and deionized water, sonication in a mixture of acetone/ethanol (1:1 v/v) for 30 min, sonication in a mixture of acetone/isopropanol (1:1 v/v) for 30 min and drying with compressed air and then heating up to 80°C for 30 min. After that, UV-ozone treatment was performed for 15 min. To prepare the TiO2 blocking layer (bl-TiO2), titanium diisopropoxide dis(acetylacetonate) (Sigma-Aldrich, 75 wt% in isopropanol) in ethanol (1:9 v/v) was deposited by spray pyrolysis at 450°C with oxygen as carrier gas and then annealed at 450°C for 30 min in air. A Au sol is prepared based Turkevich procedures [17]. An average diameter of Au was around 11 nm. Au@SiO2 core-shell NPs were prepared according to the synthetic protocol of Liz-Marzan [18]. The thickness of silica shell was about 1.4 nm. A thin layer of Au@SiO2 was deposited by spin coating on the top and the bottom of the mp-TiO2 layers and then annealed at 100°C for 10 min. A diluted commercial TiO2 paste (DSL 30NRT, Dyesol) in ethanol (1:5, weight ratio) was then deposited on the bl-TiO2 by spin-coating at 2000 rpm for 10 seconds. After drying at 100°C for 10 min, annealed in air up to 500°C for 30 min. Lithium bis-(strifluoromethane sulfonamide) (LiTFSI) 35 mM solution in acetonitrile was deposited by spin coating onto the substrates at 3000 rpm for 10 seconds. Then the films were annealed at 450°C for 30 minutes [19]. 622 mg of PbI2 (TCI, 99.999%), 214 mg of CH3NH3I (Dyesol), and 105 mg of DMSO (molar ratio 1:1:1) was mixed in 944 mg of DMF solution inside a glove box. The completely dissolved solution was spin-coated on the mp-TiO2 layers at 4000 rpm for 50 seconds. Five seconds after rotation, diethyl ether was dripped on the rotating substrate before it becomes dark color due to the rapid vaporization of DMF [20]. After depositions, layers were heated at 100°C for 3 min and a dense CH3NH3PbI3 film was obtained. Then spiro-OMeTAD based HTL (72.3 mg spiro-OMeTAD, 28.8 μL 4-tert-butyl pyridine (tBP) and 17.5 μL Li-TFSI solution (520 mg/mL of Li-TFSI in acetonitrile) all dissolved in 1 mL chlorobenzene and then deposited on perovskite layer by spin-coating at 4000 rpm for 30 seconds. The cells were dried at 100°C for 3 min. Finally, the devices were transferred into a vacuum chamber for deposition of 60 nm Au by thermal evaporation in high vacuum system to form the electrode contacts.

B. Characterization Methods

The current-voltage curves were measured with a scan rate of 50 mV/s in Abet Technologies Sun 2000 Class A solar simulator with a Keithley 2612 Source Meter, AM1.5G where the light intensity was adjusted with an NREL-calibrated Si solar cell with a KG-5 filter to 1 sun of intensity (100 mW/cm²). The measurements were performed using a shadow mask whose area was 0.101 cm². The morphology of the films was analyzed by scanning electron microscopy (SEM) using a JSM7001F (Field emission scanning electron microscope) and IPCE spectra were measured in air using a xenon lamp power source coupled with a monochromator controlled by a computer and optical power meter (Oriel Instruments, model 7310) and a Si photodiode to calibrate the system. UV-Visible absorption measurement was carried out using a double-beam spectrophotometer (JASCO, model 7800, Tokyo, Japan).

III. RESULTS AND DISCUSSION

Figure 3 displays a cross-sectional SEM image of FTO/ bl-TiO2/ Au@SiO2/ mp-TiO2/ CH3NH3PbI3/ Spiro/ Au. NPs were approximately spherical in shape. The thickness of bl is approximately 44 nm. The Au@SiO2/ mp-TiO2 layer is about 260 nm; and the CH3NH3PbI3 perovskite was infiltrated into the pore of the mp-TiO2 layer. A 270-nm-thick film of CH3NH3PbI3 perovskite is clearly seen as the final layer. The thickness of spiro-
OMeTAD and Au is about 100 nm and 60 nm respectively.

As shown in Fig. 4, the absorption of Au@SiO₂ NPs was determined by UV–Vis spectrophotometry. A resonant peak in wavelengths around 659 nm is observed. The structure of FTO/ bl-TiO₂/ Au@SiO₂/ mp-TiO₂ layers have similar optical properties like the structure consisting FTO/ bl-TiO₂/ mp-TiO₂/ Au@SiO₂. No significant change is observed in the light absorption at the 500–650 nm wavelength region of compact/mp-TiO₂ layers with and without interfacial Au@SiO₂ NPs as shown in fig. 4. These observations rule out a direct plasmonic effect by an increase of light absorption in the solar cell enhancement observed when NPs are used at the interface.

The J-V curves of the references cells and modified cells with Au@SiO₂ NPs were measured under AM1.5 ((100 mW.cm⁻²)) in air (Fig. 5). The maximum power conversion efficiency (PCE) for the reference, FTO/ bl-TiO₂/ Au@SiO₂/ mp-TiO₂, and FTO/ bl-TiO₂/ mp-TiO₂/ Au@SiO₂ cells are 14.75, 17.55, and 15.00%, respectively. An Enhancement of 5% in short-circuit current density is observed for the cells consisting Au@SiO₂ bottom the mp-TiO₂ layers compared to the reference cells. The maximum J_{sc} are 20.7 and 19.7 mA/cm², respectively. The J_{sc} of cells consisting Au@SiO₂ top the mp-TiO₂ layer was almost close to the reference cells which suggests is due to the poor plasmonic effect due to the NPs size and position.
The $J_{sc}$ value was consistent with that included from the incident-photon-to-current-efficiency (IPCE) spectra (Fig. 6). The Fig. 6 shows Au@SiO$_2$ NPs enhance charge separation. Modified cells with Au@SiO$_2$ NPs demonstrate an enhancement over the total wavelength range (300–800 nm) compared to the reference cells.

The results of reverse of the J–V measurements for 20 devices carried out at 1 sun illumination intensity are presented in Table 1. From Table 1, we observed that the average J–V scanned PCE enhancement for the FTO/ bl-TiO$_2$/ Au@SiO$_2$/ mp-TiO$_2$ compared to FTO/ bl-TiO$_2$/ mp-TiO$_2$/ Au@SiO$_2$ and the reference cells, mainly comes from the greatly improved short-circuit photocurrent density ($J_{sc}$) and the open-circuit voltage ($V_{oc}$), while fill factor (FF) are only slightly changed. Figure 7 shows the average device performance parameters of cells with dissimilar place of Au@SiO$_2$ NPs as well as the reference cells. To ensure reliability of the measurements, at least 20 samples were fabricated for each model. The FF value is affected by both the shunt resistance and the series resistance of the devices. Therefore, the low fill factor may be resulted from a low shunt resistance and a high serial resistance, as shown in Table 1. The shunt resistance is lower for the reference samples, from the higher slope of the current density-potential ($J$–$V$) curve near 0 V as we can see in Fig. 5, and it results in lower solar cell performance. The low series resistance is observed in cells with Au@SiO$_2$ bottom of mp-TiO$_2$ as shown in Fig. 8. The lowest series resistance, indicating that addition of Au NPs can increase conductivity by improving mobility charge-transporters properties [8]. Interestingly, the main impact of a rising series resistance is to reduce FF, although series resistance does not affect $V_{oc}$.

Table 1. Summary of efficiency of devices discussed in this work in the reverse.

<table>
<thead>
<tr>
<th></th>
<th>$J_{sc}$ (mA/cm$^2$)</th>
<th>$V_{oc}$ (mV)</th>
<th>FF (%)</th>
<th>PCE (%)</th>
<th>$R_{shunt}$ (Ω, cm$^2$)</th>
<th>$R_{series}$ (mΩ, cm$^2$)</th>
</tr>
</thead>
<tbody>
<tr>
<td>FTO/ bl-TiO$_2$/mp-TiO$_2$</td>
<td>19.1±0.5</td>
<td>973±30</td>
<td>69±2</td>
<td>13.6±1.3</td>
<td>1.8×10$^4$±4.1×10$^3$</td>
<td>2868±601</td>
</tr>
<tr>
<td>FTO/ bl-TiO$_2$/Au@SiO$_2$/mp-TiO$_2$</td>
<td>20.3±0.5</td>
<td>1007±43</td>
<td>73±4</td>
<td>15.8±1.7</td>
<td>4.4×10$^7$±4.9×10$^7$</td>
<td>2560±1637</td>
</tr>
<tr>
<td>FTO/ bl-TiO$_2$/mp-TiO$_2$/Au@SiO$_2$</td>
<td>19.2±1.2</td>
<td>966±29</td>
<td>69±2</td>
<td>13.0±1.3</td>
<td>2.3×10$^2$±4.2×10$^7$</td>
<td>3291±730</td>
</tr>
</tbody>
</table>

Figure 9 depicts the electrochemical impedance spectra (EIS) and the corresponding Nyquist plots for PSCs. A Nyquist plot of impedance, $Z=Z'+Z''$, in which $Z'$ is plotted in terms of $Z''$ presenting two semicircles each of which is related to an internal interface between two different semiconductors [21]. EIS in Fig. 9 have been fitted using the equivalent circuit plotted in Fig. 10 [22]. Thereupon, the electrical behavior of the device was studied based on the equivalent circuit. In the EIS analysis, a DC potential bias was applied and overlapped...
by a sinusoidal ac potential perturbation of 25 mV over a frequency range of 0.1 Hz-1 MHz.

Fig. 9 show the Nyquist plots of PSCs with Au@SiO₂ NPs, and the reference device without NPs, which showed rather higher efficiency than that of other devices. In the equivalent circuit, a series resistor $R_S$ is the nonzero intercept on the real axis of the impedance plot, which denotes the sheet resistance of FTO and the contact resistance of FTO/TiO₂.

The first semicircle, which is related to a high-frequency arc, is associated with the diffusion of holes through the perovskite/Au counter electrode interface, which is modeled by an $R_{CE}$ resistance. The arc was related to the recombination resistance, $R_{rec}$, in lower the frequency response, mainly due to the electron-hole recombination of at the mp-TiO₂/CH₃NH₃PbI₃ interface.

The resistance for the entire device with the Au@SiO₂ NPs was smaller than that of the reference device due to the presence of Au@SiO₂ NPs. As compared to the reference
device, the diameter of semicircles $R_{sc}$ clearly decreased after doping NPs on the top and the bottom of the mp-TiO$_2$ layer. Thus, it is suggested that Au@SiO$_2$ NPs in the device can improve not only the optical properties but also the electrical properties [21]. In the compare two position of deposition Au@SiO$_2$ NPs, it is apparent that $R_{sc}$ decreased after deposition Au@SiO$_2$ NPs on the bottom position of mp-TiO$_2$.

![Fig. 8](image-url)  
Fig. 8. (a) $R_{sh}$ (shunt resistance), (b) $R_{s}$ (series resistance). A: FTO/bl-TiO$_2$/mp-TiO$_2$, B: FTO/bl-TiO$_2$/Au@SiO$_2$/mp-TiO$_2$, C: FTO/bl-TiO$_2$/mp-TiO$_2$/Au@SiO$_2$.

![Fig. 9](image-url)  
Fig. 9. The EIS using 0.2 V as applied DC voltage for sample without NP (FTO/bl-TiO$_2$/mp-TiO$_2$) and with difference deposition place NPs (FTO/bl-TiO$_2$/Au@SiO$_2$/mp-TiO$_2$) and FTO/bl-TiO$_2$/mp-TiO$_2$/Au@SiO$_2$) (a) complete spectra; (b) zoom of different region of the complete plot.

![Fig. 10](image-url)  
Fig. 10 Equivalent circuit model employed for impedance analysis of the perovskite solar cells.

**IV. CONCLUSION**

In conclusion, we have synthesized Au@SiO$_2$ NP. They were then deposited bottom and top of mesoporous TiO$_2$ layer. The effect of using these NPs on the performance of the fabricated cells were studied. Although we expected an increase in $J_{SC}$, $V_{OC}$, and $FF$ for both structures, the cells with FTO/ bl-TiO$_2$/Au@SiO$_2$/mp-TiO$_2$ structure showed significant enhancement in photocurrent response compared to the reference cells. Although both cells consisting FTO/ bl-TiO$_2$/Au@SiO$_2$/mp-TiO$_2$ and FTO/ bl-TiO$_2$/mp-TiO$_2$/Au@SiO$_2$ structures show similar absorption in the visible region. However, fabricated cells have different photovoltaic properties. The FTO/ bl-TiO$_2$/Au@SiO$_2$/mp-TiO$_2$ cells also demonstrate improved IPCE compared to the reference cell, suggesting suitable surface engineering of the structure with an enhancement over the total wavelength visible range compared to the reference cells.
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